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TABLE OF CONTENTS

Understanding Inter-Chip Oscillations in Paralleled SiC MOSFETs	1
<i>A. Maitra, D. Xie, C. Bäumlér, M. Weber, T. Basler</i>	
Comparative Evaluation of Three-Phase SiC-Based Voltage/Current-Source Inverter Motor Drives.....	7
<i>Paolo Sbabo, David Menzi, Luc Imperiali, Paolo Mattavelli, Johann W. Kolar, Jonas Huber</i>	
A 200V Monolithic GaN Half-Bridge with Active Gate Driver Including a Fast dv/dt Feedback Loop	13
<i>Joseph Kemdeng, Marc Cousineau, Nicolas Rouger</i>	
Comparative Analysis of the Characteristics of Schottky-Type and Ohmic-Type p-GaN Gate GaN HEMTs	19
<i>Xiaomeng Geng, Nick Wieczorek, Benedikt Kohlhepp, Sibylle Dieckerhoff</i>	
On the Design and Effectiveness of Isolation Trenches to Suppress Substrate Coupling in Power Integrated Circuits in GaN-On-Si Technology	25
<i>Zijin Jiang, Rui Yao, Miao Cui, Zhao Wang, Sang Lam, Stephen Taylor</i>	
Three Different Designs of Integrated Gate Drivers in 650-V e-Mode GaN Power IC.....	30
<i>Plinio Bau, Thanh Hai Phung, Johan Delaine, Stephane Driussi, Thomas Beauchene</i>	
Neutron Radiation-Induced Failure Rate of 650 V Lateral GaN Power Devices	36
<i>Leon Fauth, Christian Beckemeier, Maximilian Goller, Josef Lutz, Thomas Basler, Jens Friebe</i>	
A Simplified Method for SiC Mosfet Spice Models Creation	41
<i>Oleksii Zinchenko, Dinumol Varghese, Jose Ortiz Gonzalez, Philip Mawby</i>	
Contributions to Designing Undervoltage Lockout Circuits in p-GaN Gate Technology	47
<i>Plinio Bau, Stephane Driussi, Thomas Beauchene</i>	
Design of a 650V 400A Half-Bridge GaN Power Module	52
<i>Michael Nicholson, Matthew Packwood, Daniel Bell, Xiang Li</i>	
A Comparative Evaluation of the Surge Current Robustness of Modern Power Transistors.....	57
<i>Theofilos Moraitis, Georgios Kampitsis</i>	
Double-Voltage Short-Circuit Protection Circuit for SiC MOSFETs with Temperature Compensation.....	63
<i>Yuhua Quan, Tiantian Liu, Xuotong Zhou, Junhong Feng, Wenyu Lu, Yufei Tian, Li Zheng, Xinhong Cheng</i>	
Enhancing High-Power-Density Converter Design: A Data-Driven Analysis of MOSFET and Heatsink Selection.....	68
<i>Tian Jin, Wenlong Ming, Zhengyang Feng, Manish Kumar, Sheng Wang</i>	
Sputtering Grown Wide Band Gap AlN Thin Films for High Power Capacitors	74
<i>Renjun Liu, Chandra Kant, Diyar Mousa Othman, David Macdonald, Serena Nur Erkizan, William Solari, Hong Ji, Ingo Ludtke, Wenlong Ming, Bo Hou</i>	
A Short Circuit Testing and Ruggedness Study of Latest SiC MOSFETs	77
<i>Usman Nasir, Jixuan Wei, Alex George, Mark Bowkett, Ubaid Akbar, Gerardo Calderon-Lopez, Ingo Lüdtke</i>	

Integrating Wide Bandgap Semiconductor Technologies into Emerging Mobile Energy Supply Systems.....	83
<i>Kaiqing Qiu, Yufeng Wang, Yue Zhou, Wenlong Ming, Jianzhong Wu</i>	
Wide Bandgap Power Electronic Devices for Constraint Management in Distribution Networks.....	87
<i>Xun Jiang, Yufeng Wang, Yue Zhou, Wenlong Ming, Jianzhong Wu</i>	
Soft-Switched SiC Based DC-DC Converter with Low-Loss Modulation in DC-AC Inverter for Highly Efficient EV/HEV Powertrains.....	93
<i>Hafsa Qamar, Haleema Qamar</i>	
On-Wafer RON Degradation Analysis of 100 V p-GaN HEMTs Emulating Low- and High-Side Operation in Half Bridge Circuits	97
<i>Lorenzo Modica, Nicolò Zagni, Davide Orlandini, Marcello Cioni, Giacomo Cappellini, Maria Eloisa Castagna, Giovanni Giorgino, Ferdinando Iucolano, Giovanni Verzellesi, Alessandro Chini</i>	
Monolithically Integrated Two-Stage GaN Gate Drivers	101
<i>Michael Basler, Richard Reiner, Stefan Mönch, Daniel Grieshaber, Fouad Benkhelifa, Rüdiger Quay</i>	
Steady-State Analysis of Standalone Vertical Silicon & SiC NPN BJTs	106
<i>Chengjun Shen, Saeed Jahdi, Mana Hosseinzadehlish, Phil Mellor, Konstantinos Floros, Ingo Ludtke</i>	
The Impact of Varying the High-Temperature Post-Deposition Anneal Time Or Temperature Ramp Rates on ALD-SiO ₂ /4H-SiC Interfaces	112
<i>X. Tian, A. B. Renz, A. Su, N. S. Agbo, P. Taylor, P. A. Mawby, P. M. Gammon</i>	
Impact of Temperature on Dynamics and Reliability of High-Voltage Silicon & 4H-SiC Bipolar Junction Transistors	117
<i>Mana Hosseinzadehlish, Saeed Jahdi, Xibo Yuan, Renze Yu, Jose Ortiz-Gonzalez, Olayiwola Alatise</i>	
Self-Heating and Hotspots in GaN HEMTs with Conventional and T-Shape Gates	123
<i>B. Ubochi, K. Ahmeda, M. Elksne, B. Benbakhti, A. Al-Khalidi, E. Wasige, K. Kalna</i>	
Scaling Down Megawatt-Level SSTs: Prototype Design and Performance Evaluation.....	127
<i>Ahmed Topkil, Mohamed Taha, Alan Walker, Jose Ortiz Gonzalez</i>	
An Experimental Performance Comparison of GaN and Silicon Based FETs in an Emergency LED Driver	133
<i>Ben Stainthorpe, Mohamed Dahidah, Volker Pickert</i>	
A Temperature-Related Simulink Model of Single-Stage Thermoelectric Modules.....	139
<i>Hong Li, Jinpeng Zhang, Xu Shanguan</i>	
Experimental Results on Electrical Characteristics of 2DEG Resistors in GaN-On-Si Technology	144
<i>Zixuan Zhang, Ruolan Shi, Miao Cui, Sang Lam</i>	
Thermal Performance Improvement Potential of Top and Bottom-Cooled Power-SOIC Devices.....	149
<i>Heaklig Ayala, George Rowley, Lewis Stroud, Tim Rumney, James Cotty, Philip Mawby, Jose Ortiz-Gonzalez</i>	

Author Index